

650V, 10A, Trench FS Gen.7 IGBT

General Description

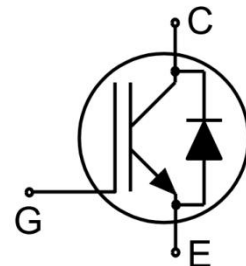
Using RST's proprietary high density trench gate design and advanced FS (Field Stop) Gen.7 technology, the 650V Trench Field Stop Gen.7 IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench Field Stop Gen.7 Technology Offering
- Low saturation voltage: $V_{CEsat} = 1.60V(Typ.) @ I_C = 10A$
- High speed switching, Low switching losses
- High ruggedness, temperature stable behavior
- Maximum junction temperature $T_{vjmax} = 175^{\circ}C$
- Easy paralleling capability due to positive temperature coefficient in V_{CEsat}
- Tighten parameter distribution
- Pb-free lead plating; RoHS compliant

Application

- Air Condition
- Inverters
- Motor drives



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
RSTBG10T65	TO-263-2L	



TO-263-2L

Absolute Maximum Ratings ($T_c=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate- Emitter Voltage	± 30	V
I_C	Collector Current	20	A
	Collector Current @ $T_C = 100^{\circ}C$	10	A
I_{Cpuls}	Pulsed Collector Current, t_p limited by T_{jmax}	20	A
-	Turn off safe operating area, $V_{CE}=650V$, $T_j=175^{\circ}C$	20	A
I_F	Diode Continuous Forward Current @ $T_C = 100^{\circ}C$	10	A
I_{FM}	Diode Maximum Forward Current	20	A
P_D	Power Dissipation @ $T_C = 25^{\circ}C$	65	W
	Power Dissipation @ $T_C = 100^{\circ}C$	33	W
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}C$
T_{vj}	Operating junction temperature	-40 to +175	$^{\circ}C$
T_L	Maximum Temperature for Soldering	260	$^{\circ}C$
t_{sc}	Short circuit withstand time $V_{GE}=15V$, $V_{CC} \leq 400V$, Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0s$, $T_j \leq 150^{\circ}C$	5	us

Thermal Characteristic

Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction to case for IGBT	2.30	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction to case for FRD	2.00	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	$^{\circ}\text{C/W}$

Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

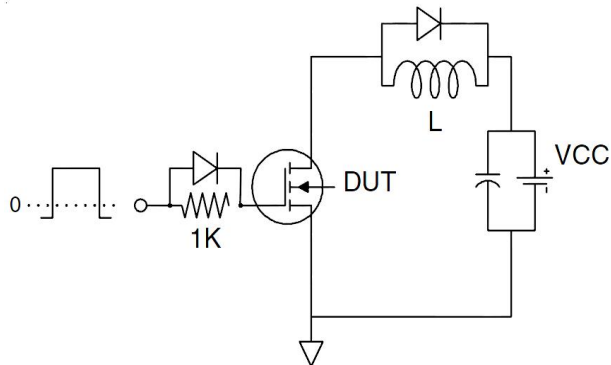
Symbol	Parameter	Conditions		Value			Units
				Min.	Typ.	Max.	
Static Characteristics							
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage	$V_{GE}=0V, I_{CE}=250\mu A$		650	--	--	V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0V, V_{CE}=650V$		--	--	2.0	μA
$I_{GES(F)}$	Gate to Emitter Forward Leakage	$V_{GE}=+30V, V_{CE}=0V$		--	--	100	nA
$I_{GES(R)}$	Gate to Emitter Reverse Leakage	$V_{GE}=-30V, V_{CE}=0V$		--	--	100	nA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=3A$	$V_{GE}=15V,$	--	1.25	--	V
		$I_C=10A$	$T_J=25^{\circ}C$	--	1.60	2.20	V
		$I_C=3A$	$V_{GE}=15V,$	--	1.35	--	V
		$I_C=10A$	$T_J=150^{\circ}C$	--	1.90	--	V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=250\mu A, V_{CE}=V_{GE}$		3.50	4.25	5.00	V
Dynamic Characteristics							
C_{ies}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$		270	340	410	pF
C_{oes}	Output Capacitance			--	12	--	
C_{res}	Reverse Transfer Capacitance			--	7	--	
Q_g	Total Gate Charge	$V_{CE}=480V, I_C=10A,$ $V_{GE}=15V$		--	17.7	--	nC
Q_{ge}	Gate to Emitter Charge			--	3.2	--	
Q_{gc}	Gate to Collector Charge			--	7.2	--	
R_g	Internal Gate Resistance	F=1MHz		--	3.0	--	Ω
$I_{C(SC)}$	Short circuit collector current Max.1000 short circuits Time between short circuits: $\geq 1.0s$	$V_{GE}=15V, V_{CC}\leq 400V,$ $t_{SC}\leq 5\mu s, T_J\leq 150^{\circ}C$		--	18	--	A
Switching Characteristics							
$t_{d(ON)}$	Turn-on Delay Time	$V_{CE}=400V, I_C=6A,$ $V_{GE}=0/15V, R_g=25\Omega$ Inductive Load		--	24	--	ns
t_r	Rise Time			--	13	--	
$t_{d(OFF)}$	Turn-Off Delay Time			--	105	--	
t_f	Fall Time			--	19	--	
E_{on}	Turn-On Switching Loss			--	0.21	--	mJ
E_{off}	Turn-Off Switching Loss			--	0.10	--	
E_{ts}	Total Switching Loss			--	0.31	--	

Electrical Characteristics of the Diode ($T_c = 25^\circ\text{C}$ unless otherwise specified)

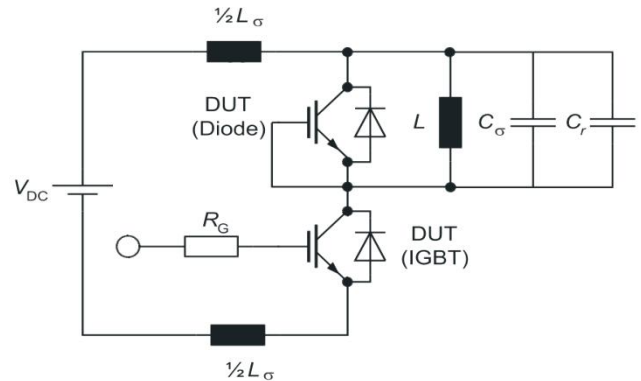
Symbol	Parameter	Conditions		Rating			Units
				Min.	Typ.	Max.	
V_{FM}	Diode Forward Voltage	$I_F = 6\text{A}$	$T_j = 25^\circ\text{C}$	--	2.0	2.6	V
			$T_j = 175^\circ\text{C}$	--	2.1	--	
T_{rr}	Reverse Recovery Time	$V_{CE} = 400\text{V}, I_F = 10\text{A},$ $R_g = 25\Omega, T_j = 25^\circ\text{C}$		--	87	--	ns
I_{RRM}	Diode Peak Reverse Recovery Current			--	1.13	--	A
Q_{rr}	Reverse Recovery Charge			--	0.05	--	μC

Test Circuit

1) Gate Charge Test Circuit

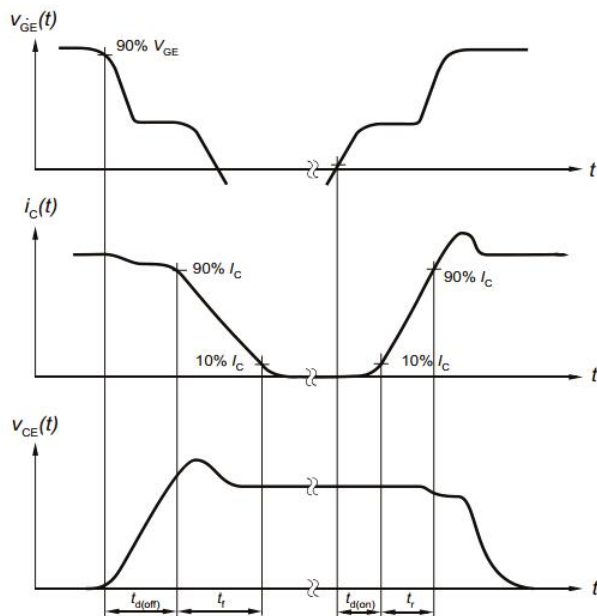


2) Switch Time Test Circuit

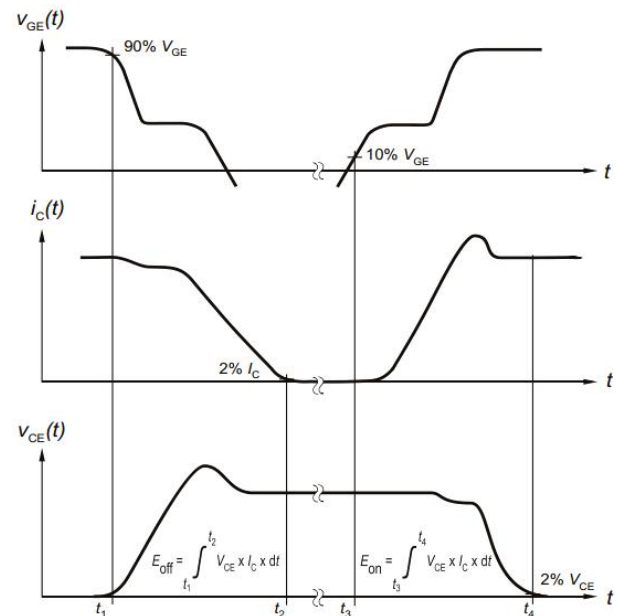


Switching characteristics

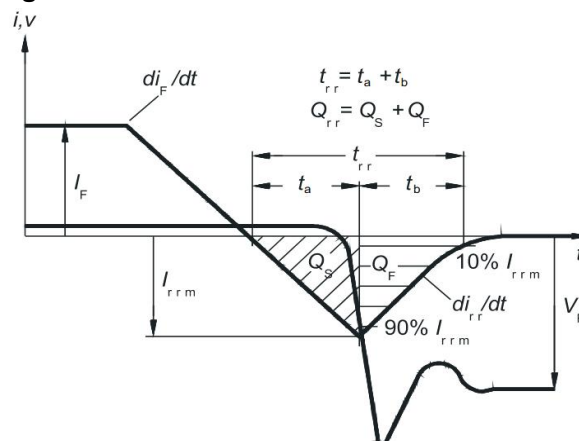
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

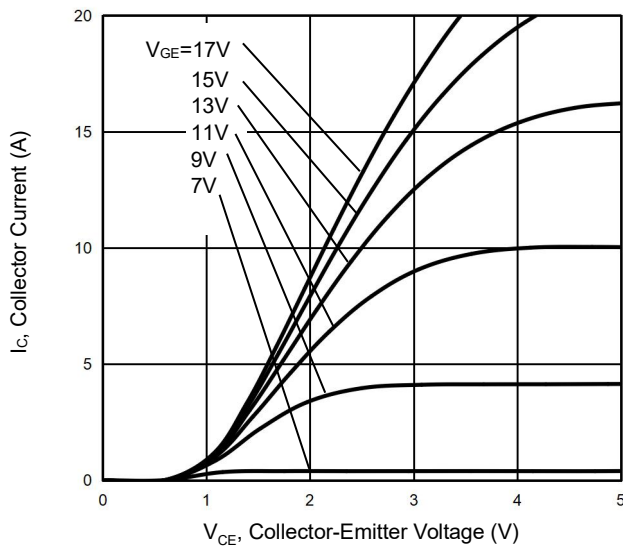


Figure 2 Transfer Characteristics

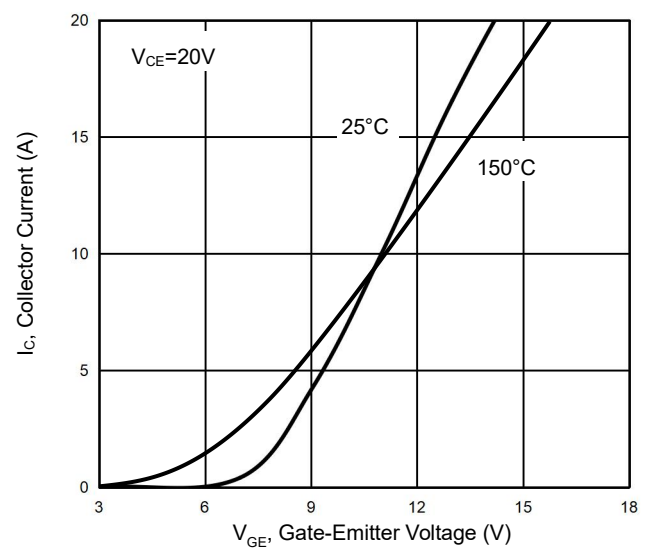


Figure 3 $V_{CE(sat)}$ vs. Case Temperature

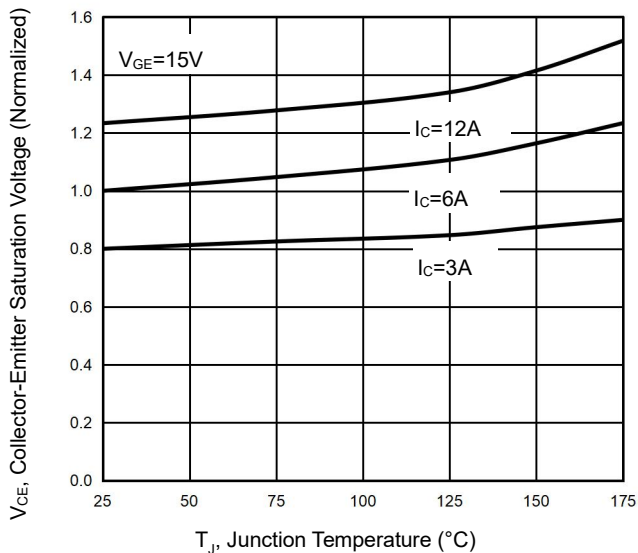


Figure 4 Saturation Voltage vs. V_{GE}

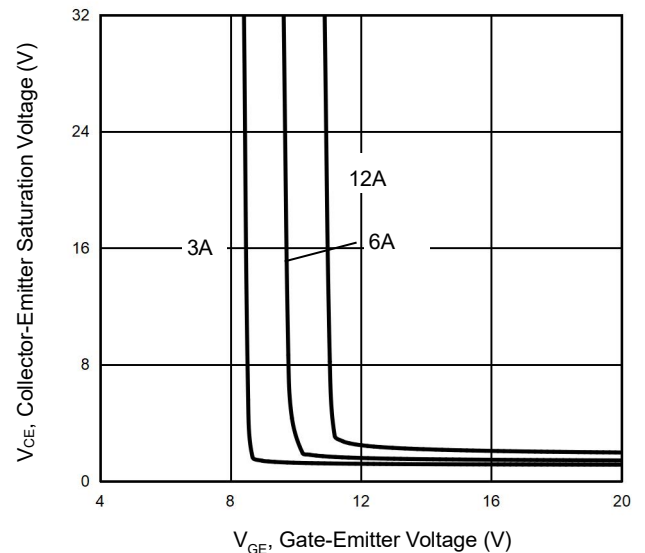


Figure 5 Capacitance Characteristics

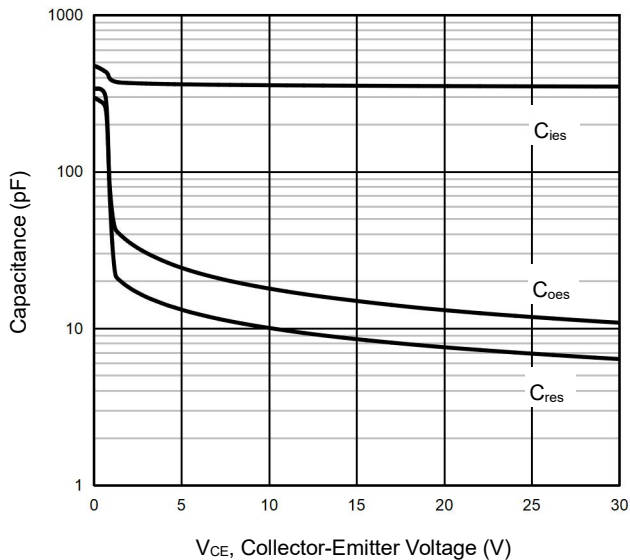
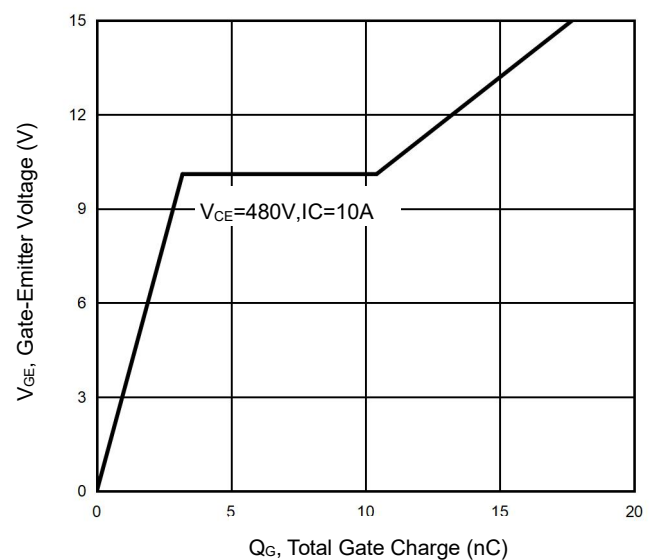


Figure 6 Gate Charge Wave Form



Typical Electrical and Thermal Characteristics

Figure 7 Forward Characteristics

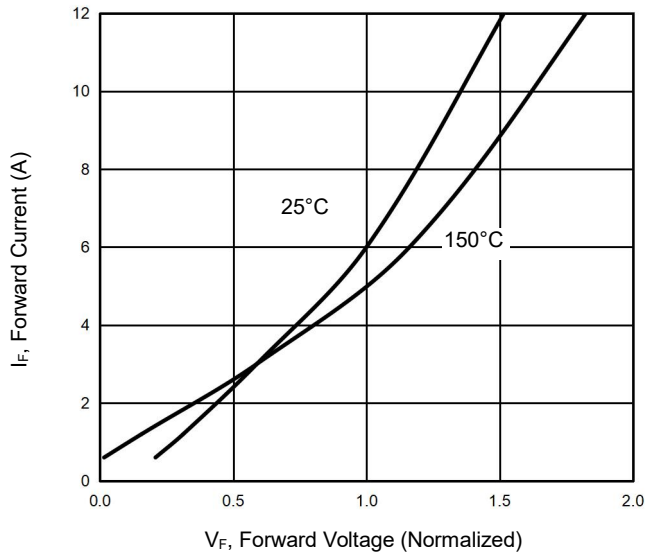


Figure 8 V_F vs. Temperature

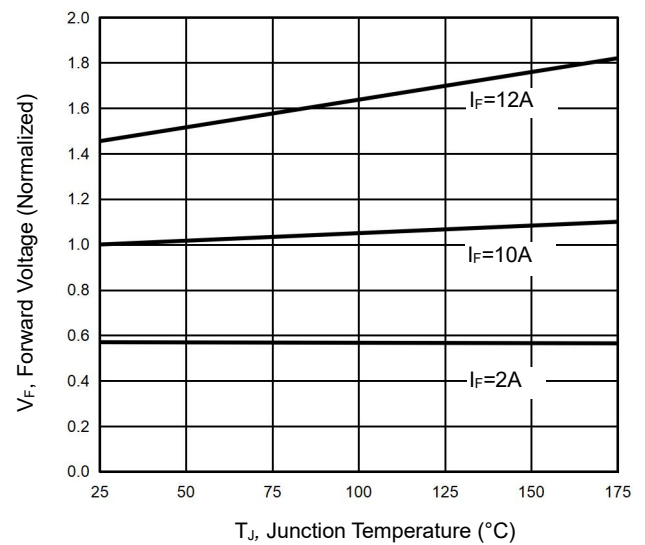


Figure 9 P_{tot} vs. Case Temperature

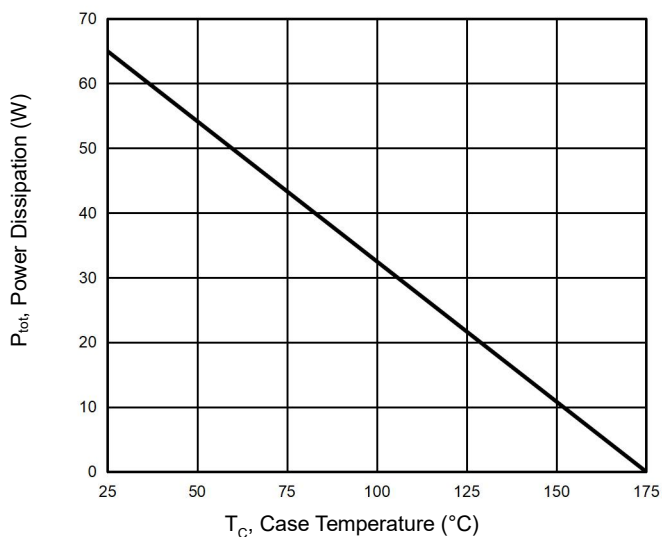


Figure 10 Forward Bias Safe Operating Area

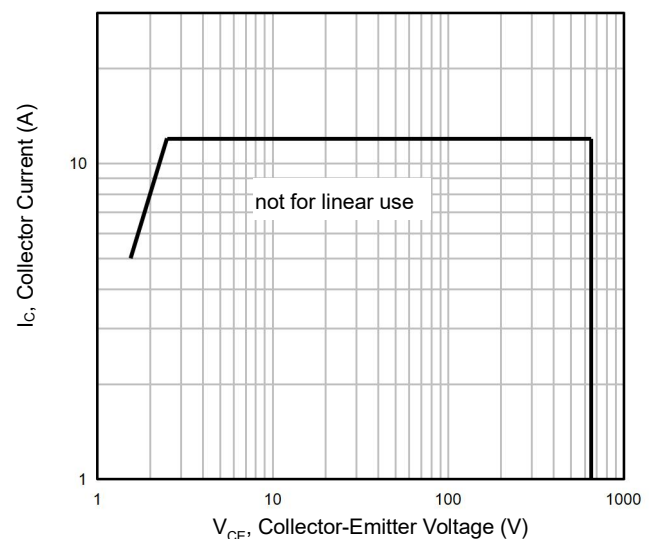


Figure 11 Gate-Emitter Threshold Voltage as a Function of Junction Temperature

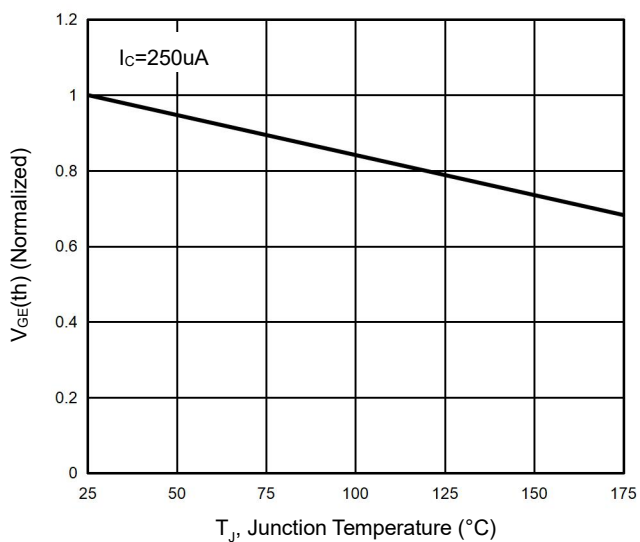
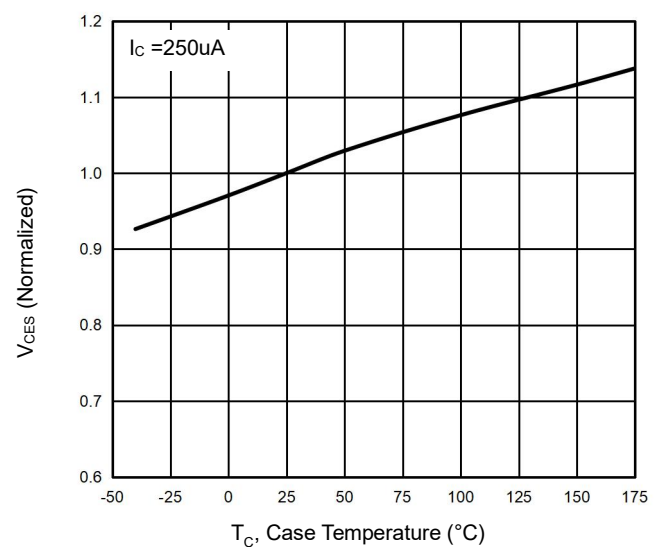
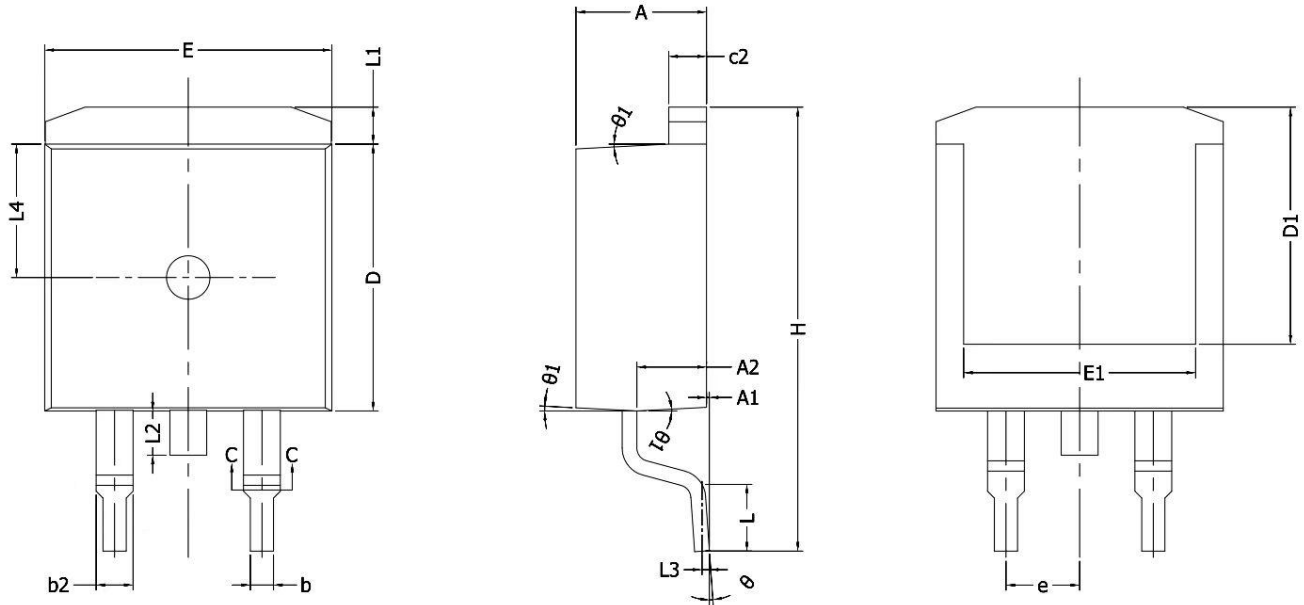


Figure 12 V_{CES} vs. Case Temperature



TO-263-2L-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.17	0.18
A1	0.00	0.25	0.00	0.01
A2	2.20	2.60	0.09	0.10
b	0.76	0.89	0.03	0.04
b2	1.23	1.37	0.05	0.06
C	0.47	0.60	0.02	0.03
c2	1.25	1.35	0.05	0.06
D	9.10	9.30	0.35	0.36
D1	8.00	-	0.31	-
E	9.80	10.00	0.39	0.40
E1	7.80	-	0.31	-
e	2.54BSC		0.10BSC	
H	14.90	15.70	0.59	0.62
L	2.00	2.60	0.08	0.10
L1	1.17	1.40	0.05	0.06
L2	-	1.75	-	0.07
L3	0.25BSC		0.01BSC	
L4	4.60REF		0.18REF	
θ	0°	8°	0°	8°
θ1	1°	5°	1°	5°